

REMARKS

Claims 1 - 28 are pending in the present application, of which claims 1 – 9 and 13 – 24 have been withdrawn from consideration. By this Amendment, claim 10 has been amended. No new matter has been added. It is respectfully submitted that this Amendment is fully responsive to the Office Action dated November 7, 2003.

Allowable Claim Subject Matter:

Applicants gratefully acknowledge the indication in item 5 of the Office Action that claims 25 and 26 would be allowable, if amended, to include all of the limitations of the base claim and any intervening claims.

However, for at least the reasons discussed below, it is respectfully submitted that all of claims 10 – 12 and 25 - 28 are allowable.

As To The Merits

As to the merits of this case, the Examiner sets forth the following rejections:

1) claims 10, 11 and 28 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Chang et al. (U.S. Patent No. 5,610,088) in view of Kapoor (U.S. Patent No. 5,780,350) and Wolf (Silicon Processing for the VLSI Era: Vol. 2 – Process Integration);

2) claim 12 stands rejected under 35 U.S.C. §103(a) as being unpatentable over Chang et al. in view of Kapoor and Wolf as applied to claim 10 above, and further in view of Shibata (U.S. Patent No. 4,622,735); and

3) claim 27 stands rejected under 35 U.S.C. §103(a) as being unpatentable over Chang et al. in view of Kapoor, Wolf, and Shibata as applied to claim 12 above, and further in view of Wolf et al. (Silicon Processing for the VLSI Era – Vol. 1: Process Technology).

Each of these rejections are respectfully traversed.

Claim 10, as amended, now calls for in step (c) implanting impurities of a second conductivity type opposite to said first conductivity type into a surface layer of said second region, and thereafter executing a first activation process to form first impurity diffusion region shallower than said isolation regions.

The Examiner interprets formation of the n-type well 110 in type p-type substrate 100 of Chang et al. to read on step (c) of claim 10. In Chang et al., the N-type well 110 is deeper than the isolation region 112. In contrast, in the present invention, this step forms a positive element region, such as a resistive region of a resistor. That is, as is clearly shown in Fig. 5B of the present application, the implanted region 308 is apparently shallower than the isolation region 300a.

Thus, it is respectfully submitted that claim 10 is not obvious from the combination of the applied references since while Chang et al. may disclose forming a well or a tub region which is not a positive element region, Chang et al. does not teach forming a positive first impurity diffusion region of second conductivity type shallower than the isolation region in the second region.

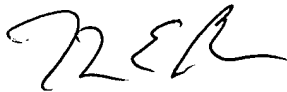
In view of the aforementioned amendments and accompanying remarks, Applicants submit that the claims, as herein amended, are in condition for allowance. Applicants request such action at an early date.

If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned attorney to arrange for an interview to expedite the disposition of this case.

Response under 37 C.F.R. §1.116
Attorney Docket No. 020200
Serial No. 10/084,367

If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,
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